

De Haas-van Alphen oscillations in ZrSiS and HfSiS

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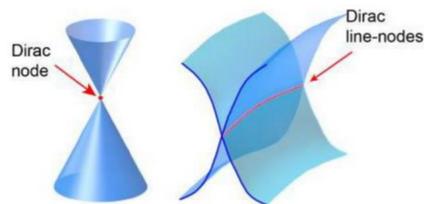
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Nodal line semimetal

Dirac nodal fermions physics:

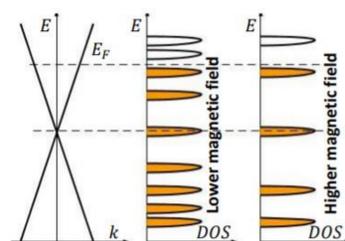
- Nontrivial topology
- Topologically protected surface states



Symmetry protected band degeneracies which form lines
Linear energy dispersion -> Dirac line nodes

Quantum oscillations

- Electrons in strong magnetic field
-> Landau levels
- Increasing field leads to periodical crossing of Landau levels and E_F
-> Oscillations of physical quantities with $1/B$
- Frequency of oscillations determined by the extremal cross sections of FS and plane normal to external field



Lifshitz-Kosevich equation

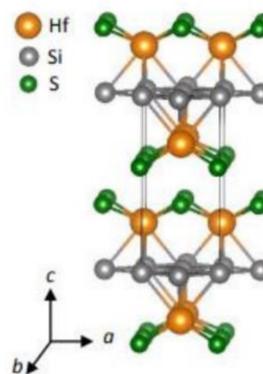
$$\Delta X(B, T) = A_0 A_T A_D A_S \left(\frac{B}{F}\right)^2 \cos\left[2\pi \frac{F}{B} + \phi\right]$$

$$A_T = -\frac{2\pi^2 \left(\frac{k_B T}{\hbar \omega_c}\right)}{\sinh\left(2\pi^2 \left(\frac{k_B T}{\hbar \omega_c}\right)\right)} \quad A_D = \exp\left(-2\pi^2 \left(\frac{k_B T_D}{\hbar \omega_c}\right)\right)$$

$$A_S = \cos[\pi g m_e / 2m_c]$$

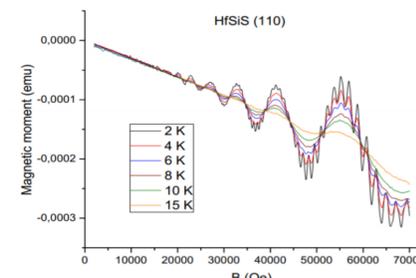
Quantum oscillations in magnetization -> de Haas-van Alphen oscillations

Hf_xZr_{1-x}SiS

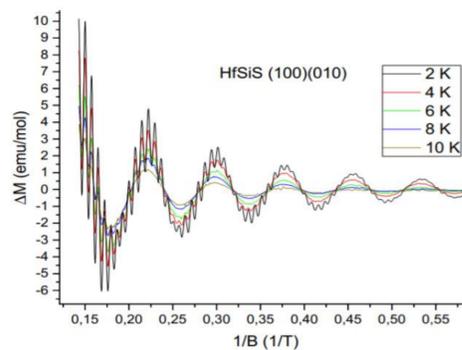


HfSiS and ZrSiS crystallize in same structure
-> possibility for substitution

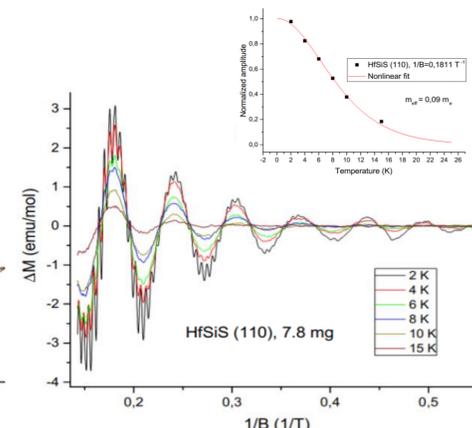
Magnetization data acquired with SQUID magnetometer up to 7 T for different ϕ and θ considering crystal symmetry



HfSiS

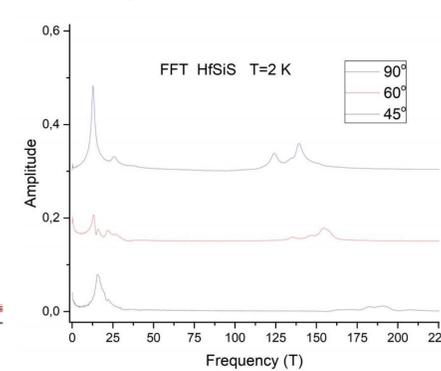
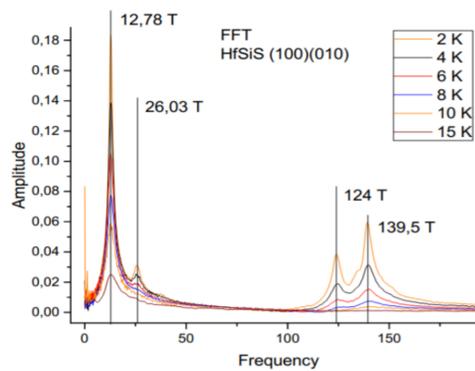


Interference of 'two groups' of frequencies

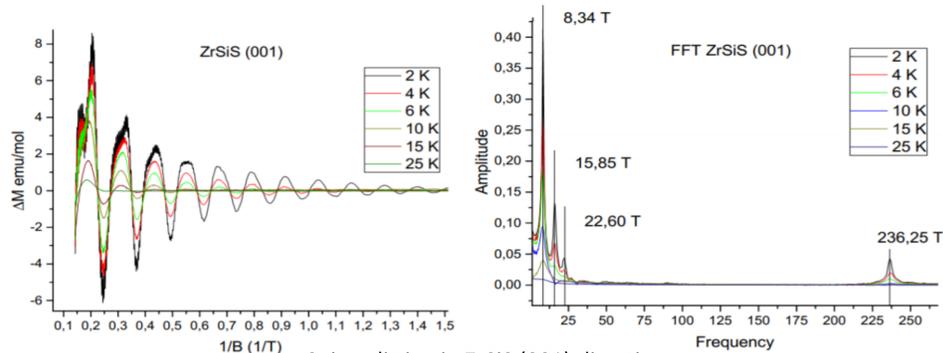


Effective mass can be obtained using LK equation

Propagation of frequencies for different ϕ

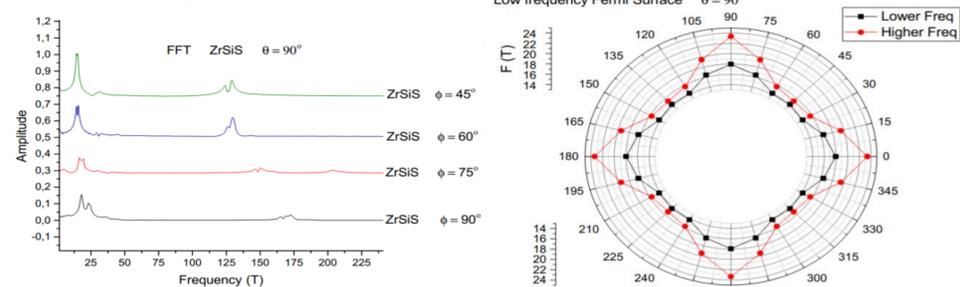


ZrSiS



Spin splitting in ZrSiS (001) direction

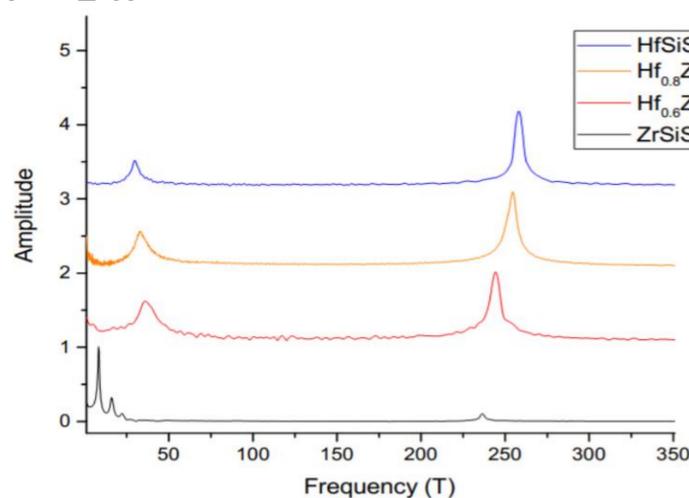
Reconstructing low frequency Fermi Surface by rotating the sample



Conclusion

- Magnetization in Hf_xZr_{1-x}SiS single crystal was measured with SQUID magnetometer up to 7 T for different angles ϕ and θ
- FFT of quantum oscillations shows two sets of frequencies: low frequencies (up to 40 T) and high frequencies between 100-250 T
- FS of selected crystal can be reconstructed from frequencies
- Measurement and synthesis of remaining Hf_xZr_{1-x}SiS compositions in progress

Hf_xZr_{1-x}SiS



Substitution effect on oscillations frequency in (001) direction
Measurement and synthesis of remaining compositions in progress

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